

| Ref # | Hits | Search Query | DBs | Default Operator | Plurals | Time Stamp |
|-------|------|---|--|------------------|---------|------------------|
| S1 | 32 | ("6483156" "20020167007" "6716684" "6475869" "20020081794" "6376317" "5716879" "5563077" "6680240" "5578513" "5658806" "6562665" "6525403" "5346839" "6413802" "6730964" "6611029"). PN. | USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | OFF | 2005/03/16 10:12 |
| S2 | 0 | S1 and metal adj film and opposite adj sidewalls | USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/03/16 10:14 |
| S3 | 1 | S1 and metal adj film | USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/03/16 10:34 |
| S4 | 83 | opposite adj sidewall and gate adj electrode and gate adj dielectric | USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/03/16 10:39 |
| S5 | 23 | opposite adj sidewall and gate adj electrode and gate adj dielectric and SOI | USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/03/16 11:22 |
| S6 | 92 | ("4589928" "5923066" "6090713" "4261761" "4863562" "5455547" "5537083" "5589082" "6218208" "6218208" "4249190" "6147381" "5952701" "4466175" "4899202" "4906587" "4946799" "4965213" "5293058" "5808346" "5930630" "6194289" "4270137" "4786609" "5397720" "5508555" "5541436" "5821575" "5877978" "5918114" "5930605" "6040212" "6060364" "6081443" "6124613" "6225662" "6225662" "6228698" "6238960" "4378628" "4460911" "4476545" "4599576" "4823180" "4929991" "4969022" "5442584" "5504027" "5663578" "5696396").pn. | USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/03/16 10:44 |
| S7 | 1 | opposite adj sidewall near5 semiconductor adj body and gate adj electrode and gate adj dielectric and SOI | USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/03/16 11:23 |

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| S8 | 13 | ("20020081794" "20020167007" "5563077" "5578513" "5658806" "5716879" "6376317" "6413802" "6475869" "6483156" "6611029" "6680240" "6716684").PN. | US-PGPUB; USPAT; USOCR | OR | OFF | 2005/03/16 12:53 |
| S9 | 6180 | gate electrode and work function and metal film | US-PGPUB; USPAT; USOCR | AND | OFF | 2005/03/16 12:53 |
| S11 | 3561 | gate electrode and work function same metal film | US-PGPUB; USPAT; USOCR | AND | ON | 2005/03/16 12:55 |
| S12 | 1901 | gate electrode same work function same metal film | US-PGPUB; USPAT; USOCR | AND | ON | 2005/03/16 12:56 |
| S13 | 847 | gate electrode same work function same metal film and p-type | US-PGPUB; USPAT; USOCR | AND | ON | 2005/03/16 12:56 |
| S14 | 49 | gate electrode same work function same metal film | US-PGPUB; USPAT; USOCR | ADJ | ON | 2005/03/16 12:59 |
| S15 | 350 | work function same metal film | US-PGPUB; USPAT; USOCR | ADJ | ON | 2005/03/16 12:59 |
| S16 | 149 | work function same metal film and gate electrode | US-PGPUB; USPAT; USOCR | ADJ | ON | 2005/03/16 12:59 |
| S17 | 4 | "6858478".pn. "20040142567".pn. | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/11/03 11:01 |
| S18 | 34 | ("20020081794" "20020167007" "5346839" "5563077" "5578513" "5658806" "5716879" "6376317" "6413802" "6475869" "6483156" "6525403" "6562665" "6611029" "6680240" "6716684" "6730964").PN. | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/11/03 12:58 |
| S19 | 296 | "18" and workfunction | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/11/03 12:58 |

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| S20 | 34 | ("20020081794" "20020167007" "5346839" "5563077" "5578513" "5658806" "5716879" "6376317" "6413802" "6475869" "6483156" "6525403" "6562665" "6611029" "6680240" "6716684" "6730964"). PN. | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/11/03 12:58 |
| S21 | 1 | S20 and workfunction | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/11/03 13:14 |
| S22 | 99 | gate adj electrode same workfunction | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/11/03 14:53 |
| S23 | 260 | gate same workfunction | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/11/03 14:58 |
| S24 | 319 | semiconductor and workfunction | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/11/03 16:20 |
| S25 | 304 | MOS\$3 and workfunction | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/11/03 14:57 |
| S26 | 348 | S24 or S25 | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/11/03 14:57 |
| S27 | 275 | S24 and S25 | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/11/03 14:57 |
| S28 | 11 | gate same workfunction and "4.0" | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/11/03 15:00 |
| S29 | 11 | gate and workfunction and "4.0" | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/11/03 15:04 |

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| S30 | 279 | gate and workfunction and "4" | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/11/03 15:05 |
| S31 | 38 | gate and workfunction same "4" | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/11/03 15:05 |
| S32 | 1 | semiconductor and workfunction same "4\$3" | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/11/03 16:17 |
| S33 | 9 | finfet and metal adj film | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | AND | ON | 2005/11/08 12:03 |
| S34 | 403 | finfet and metal | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | AND | ON | 2005/11/08 12:03 |
| S35 | 253 | finfet and metal near5 gate | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | AND | ON | 2005/11/08 12:30 |
| S36 | 190 | finfet and metal near5 (layer or film) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | AND | ON | 2005/11/08 17:23 |
| S37 | 35 | finfet and metal near5 gate adj electrode | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | AND | ON | 2005/11/08 17:23 |